

Список публикаций оппонента Георгия Георгиевича Зегри:

- 1) Savenkov G.G., Morozov V.A., Ilyushin M.A., Poberezhnaya U.M., Freiman V.M., Zegrya A.G., Bragin V.A., Fadeev D.V., Zegrya G.G., Peculiarities of initiation by high-current electron beam of energy composites based on porous silicon with niobium boride and graphene additives, *Tech. Phys.*, v.69, 1, 2024, p. 113 – 118, <https://doi.org/10.61011/JTF.2024.01.56909.193-23>
- 2) Zegrya G.G., Ulin V.P., Zegrya A.G., Freiman V.M., Ulin N.V., Fadeev D.V., Savenkov G.G., Limiting thickness of pore walls formed in processes of anode etching of heavily doped semiconductors. *Tech. Phys.*, v.68, 2, 2023, p. 263 - 266 <https://doi.org/10.21883/TP.2023.02.55482.224-22>
- 3) Poberezhnaya U.M., Freiman V.M., Ilyushin M.A., Zegrya G.G., Fadeev D.V., Os`kin I.A., Morozov V.A., Grigor`ev A.Yu., Savenkov G.G., Optical and electron-beam initiation of porous silicon films with different contents of oxidizer and graphene. *Tech. Phys.*, v.67, 11, 2022, p. 1469 – 1474, <https://doi.org/10.21883/TP.2022.11.55177.169-22>
- 4) Savenkov G.G., Kozachuk A.I., Poberezhnaya U.M., Freiman V.M., Zegrya G.G., Combustion rate of powdered porous silicon with limited space. *Tech. Phys. Lett.*, v.48, 2, 2022, p. 51 – 53, <https://doi.org/10.21883/TPL.2022.02.52848.18994>
- 5) Bazhenov N.L., Mynbaev K.D., Semakova A.A., Zegrya G.G., Comparative Analysis of the Electroluminescence Efficiency in Type-I and Type-II Heterostructures Based on III-V Narrow-Gap Compounds. *Semiconductors*, v.56, 2, 2022, p. 43 – 49, <http://dx.doi.org/10.1134/S1063782622010043>
- 6) Morozov V.A., Zegrya A.G., Zegrya G.G., Savenkov G.G., Piezoelectric Properties of Porous Silicon. *Jetp Lett.*, v.114, 10, 2021, p. 625 – 629, <http://dx.doi.org/10.1134/S0021364021220100>
- 7) Zegrya G.G., Shashkov E.V., Karpova A.A., Vorobiev N.S., Freiman V.M., Zegrya A.G., Solomonov Y.S., Laser Effect in the Explosion of Porous Silicon. *JETP Lett.*, v.114, 4, 2021, p. 227 – 231, <http://dx.doi.org/10.1134/S0021364021160128>
- 8) Zegrya G.G., Ulin V.P., Zegrya A.G., Ulin N.V., Frayman V.M., Mikhailov Y.M., Erratum to: Effect of Conductivity Type and Doping Level of Silicon Crystals on the Size of Formed Pore Channels during Anodic Etching in Hydrofluoric Acid Solutions (Technical Physics, 2019, vol 64, 10, pg 1492, 10.1134/S1063784219100268). *Tech. Phys.*, v.66, 2, 2021, p. 367 – 367, <http://dx.doi.org/10.1134/S106378422102016X>

9) Zegrya G.G., Savenkov G.G., Zegrya A.G., Bragin V.A., Os`kin I.A., Poberezhnaya U.M., Laser Initiation of Energy-Saturated Composites Based on Nanoporous Silicon. *Tech. Phys.*, v.65, 10, 2020, p. 1636 – 1642, <http://dx.doi.org/10.1134/S1063784220100266>

10) Ageev M.V., Vedernikov Y.N., Zegrya G.G., Poberezhnaya U.M., Popov V.K., Savenkov G.G., Mechanosensitivity of Nanoporous Silicon-Based Binary Mixtures. *Tech. Phys. Lett.*, v.46, 3, 2020, p. 249 – 252, <http://dx.doi.org/10.1134/S1063785020030037>

11) Samosvat D.M., Chikalova-Luzina O.P., Zegrya G.G., Mechanism of Singlet-Oxygen Generation on the Surface of Excited Nanoporous Silicon. *Semiconductors*, v.53, 11, 2019, p. 1445 – 1456, <http://dx.doi.org/10.1134/S1063782619110162>